NCE N-Channel Super Trench Power MOSFET

Description

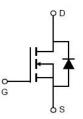
The NCEP40T17AD uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

General Features

- V_{DS} =40V,I_D =170A
 R_{DS(ON)}=1.4mΩ (typical) @ V_{GS}=10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification



Schematic Diagram



TO-263-2L top view

100% UIS TESTED! 100% ΔVds TESTED!

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP40T17AD	NCEP40T17AD	TO-263-2L	-	-	-

Absolute Maximum Ratings (T_c=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	40	V
Gate-Source Voltage	V _G s	±20	V
Drain Current-Continuous	I _D	170	A
Drain Current-Continuous(T _C =100 ℃)	I _D (100°C)	120	Α
Pulsed Drain Current	I _{DM}	680	А
Maximum Power Dissipation	P _D	250	W
Derating factor		1.66	W/°C
Single pulse avalanche energy (Note 1)	E _{AS}	1200	mJ
Operating Junction and Storage Temperature Range	T_{J},T_{STG}	-55 To 175	$^{\circ}$

Thermal Characteristic

Thermal Resistance,Junction-to-Case	Rejc	0.6	°C/W
Thermal Resistance, Junction-to-Case	К өЈС	0.6	C/VV

NCEP40T17AD

Electrical Characteristics (T_C=25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250µA	40		-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =40V,V _{GS} =0V	-	-	1	μΑ
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V _{GS(th)}	$V_{DS}=V_{GS},I_{D}=250\mu A$	2.0	3.0	4.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =85A	-	1.4	1.7	mΩ
Forward Transconductance	g FS	V _{DS} =5V,I _D =85A	-	80	-	S
Dynamic Characteristics	,		'			•
Input Capacitance	C _{lss}		-	5670	-	PF
Output Capacitance	Coss	$V_{DS}=20V, V_{GS}=0V,$	-	2550	-	PF
Reverse Transfer Capacitance	C _{rss}	F=1.0MHz	-	110	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t _{d(on)}		-	13.5	-	nS
Turn-on Rise Time	t _r	V_{DD} =20 V , I_D =85 A	-	7.2	-	nS
Turn-Off Delay Time	t _{d(off)}	$V_{\text{GS}}\text{=}10V, R_{\text{G}}\text{=}1.6\Omega$	-	55	-	nS
Turn-Off Fall Time	t _f		-	8.6	-	nS
Total Gate Charge	Qg	\/ 00\/ L 05A	-	88.6	-	nC
Gate-Source Charge	Q _{gs}	V_{DS} =20V, I_D =85A, V_{GS} =10V	-	28	-	nC
Gate-Drain Charge	Q_{gd}		-	13	-	nC
Drain-Source Diode Characteristics	,					
Diode Forward Voltage	V _{SD}	V _{GS} =0V,I _S =85A	-		1.2	V
Diode Forward Current	Is		-	-	170	Α
Reverse Recovery Time	t _{rr}	T _J = 25°C, I _F = I _S	-		33	nS
Reverse Recovery Charge	Qrr	di/dt = 100A/µs	-		119	nC

Notes:

^{2.} uaranteed by design, not subject to production

^{3.} These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsin k, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

Typical Electrical and Thermal Characteristics

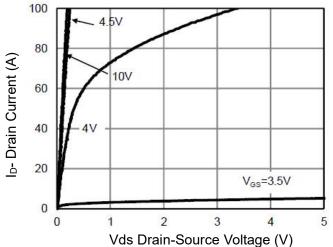


Figure 1 Output Characteristics

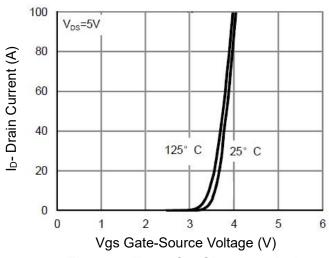


Figure 2 Transfer Characteristics

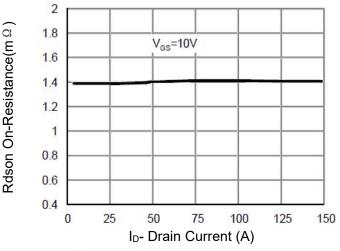


Figure 3 Rdson- Drain Current

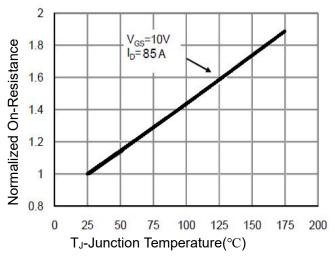


Figure 4 Rdson-Junction Temperature

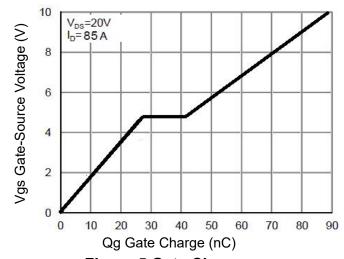


Figure 5 Gate Charge

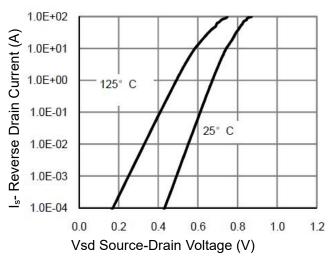
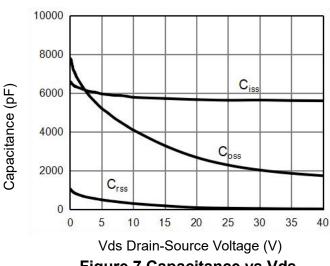


Figure 6 Source- Drain Diode Forward



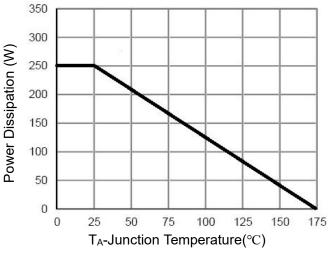
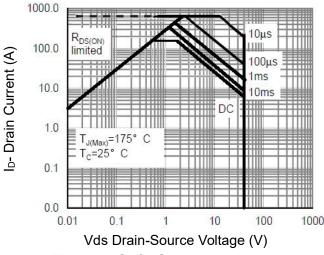


Figure 7 Capacitance vs Vds

Figure 9 Power De-rating



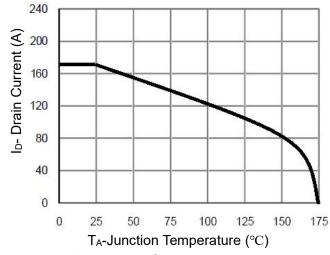


Figure 8 Safe Operation Area (Note 3)

Figure 10 Current De-rating

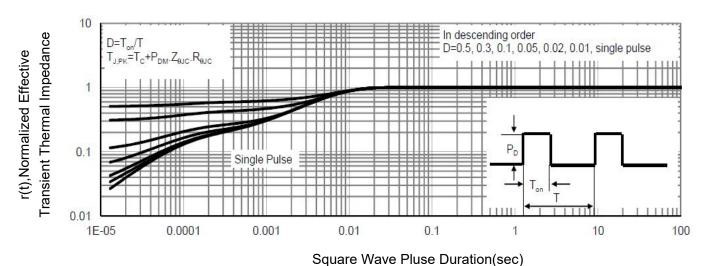
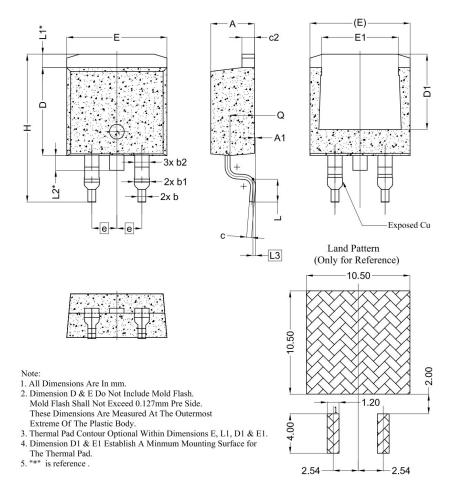


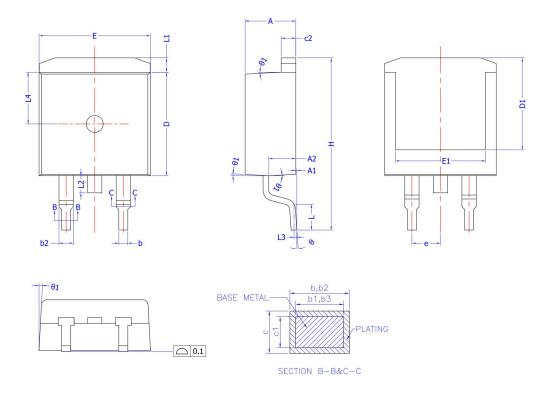
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-263-2L(G) Package Information



SYMBOL	DIMENSIONS			
STIVIBUL	MIN.	NOM.	MAX.	
А	4.24	4.44	4.64	
A1	0.00	0.10	0.25	
b	0.70	0.80	0.90	
b1	1.20	1.55	1.75	
b2	1.20	1.45	1.70	
С	0.40	0.50	0.60	
c2	1.15	1.27	1.40	
D	8.82	8.92	9.02	
D1	6.86	7.65	_	
E	9.96	10.16	10.36	
E1	6.89	7.77	7.89	
е	2.54 BSC			
Н	14.61	15.00	15.88	
Г	1.78	2.32	2.79	
L1	1.36 REF.			
L2	1.50 REF.			
L3	0.25 BSC			
Q	2.30	2.48	2.70	

TO-263-2L(P) Package Information



COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2.20	2.40	2.60	
b	0.76		0.89	
b1	0.75	0.80	0.85	
b2	1.23		1.37	
b3	1.22	1.27	1.32	
С	0.47		0.60	
c1	0.46	0.51	0.56	
c2	1.25	1.30	1.35	
D	9.10	9.20	9.30	
D1	8.00			
E	9.80	9.90	10.00	
E1	7.80			
e	2.	54 BSC		
Н	14.90	15.30	15.70	
L	2.00	2.30	2.60	
L1	1.17	1.27 1.40		
L2			1.75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	1	8°	
θ1	1°	3°	5°	

NCEP40T17AD

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